

BC846 series

65 V, 100 mA NPN general-purpose transistors

Rev. 9 — 25 September 2012

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose transistors in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number ^[1]	Package			PNP complement
	NXP	JEITA	JEDEC	
BC846	SOT23	-	TO-236AB	BC856
BC846W	SOT323	SC-70	-	BC856W
BC846T	SOT416	SC-75	-	BC856T

[1] Valid for all available selection groups.

1.2 Features and benefits

- General-purpose transistors
- SMD plastic packages
- Two different gain selections

1.3 Applications

- General-purpose switching and amplification

1.4 Quick reference data

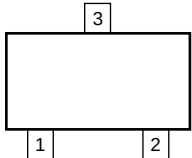
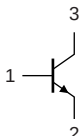
Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CE0}	collector-emitter voltage	open base	-	-	65	V
I_C	collector current		-	-	100	mA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	450	
	h_{FE} group A		110	180	220	
	h_{FE} group B		200	290	450	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT23, SOT323, SOT416			
1	base	 006aaa144	 sym021
2	emitter		
3	collector		

3. Ordering information

Table 4. Ordering information

Type number ^[1]	Package		
	Name	Description	Version
BC846	-	plastic surface-mounted package; 3 leads	SOT23
BC846W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BC846T	SC-75	plastic surface-mounted package; 3 leads	SOT416

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BC846	1D*
BC846A	1A*
BC846B	1B*
BC846W	1D*
BC846AW	1A*
BC846BW	1B*
BC846T	1M
BC846AT	1A
BC846BT	1B

[1] * = placeholder for manufacturing site code

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	80	V
V_{CEO}	collector-emitter voltage	open base	-	65	V
V_{EBO}	emitter-base voltage	open collector	-	6	V
I_C	collector current		-	100	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	200	mA
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]		
	SOT23		-	250	mW
	SOT323		-	200	mW
	SOT416		-	150	mW
T_j	junction temperature		-	150	°C
T_{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]			
	SOT23		-	-	500	K/W
	SOT323		-	-	625	K/W
	SOT416		-	-	833	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

7. Characteristics

Table 8. Characteristics

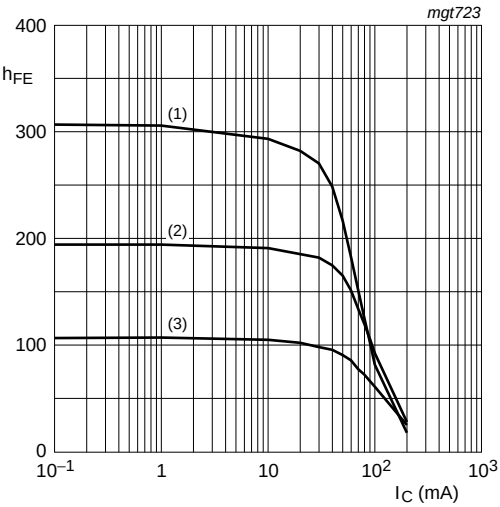
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{CBO}	collector-base cut-off current	$V_{CB} = 30\text{ V}; I_E = 0\text{ A}$	-	-	15	nA
		$V_{CB} = 30\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	5	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 10\text{ }\mu\text{A}$				
	h_{FE} group A		-	180	-	
	h_{FE} group B		-	290	-	
	DC current gain	$V_{CE} = 5\text{ V}; I_C = 2\text{ mA}$	110	-	450	
	h_{FE} group A		110	180	220	
	h_{FE} group B		200	290	450	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	-	90	200	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[1] -	200	400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	[2] -	760	-	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	[2] -	900	-	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	[3] 580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}$	[3] -	-	770	mV
f_T	transition frequency	$V_{CE} = 5\text{ V}; I_C = 10\text{ mA}; f = 100\text{ MHz}$	100	-	-	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_E = 0\text{ A}; f = 1\text{ MHz}$	-	2	3	pF
C_e	emitter capacitance	$V_{EB} = 0.5\text{ V}; I_C = I_C = 0\text{ A}; f = 1\text{ MHz}$	-	11	-	pF
NF	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	-	2	10	dB

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta = 0.02$.

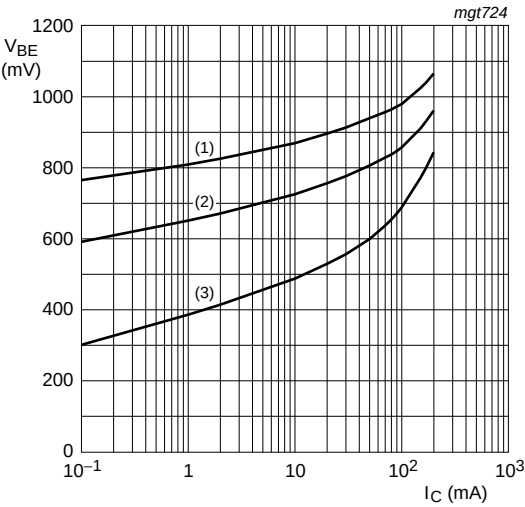
[2] V_{BEsat} decreases by approximately 1.7 mV/K with increasing temperature.

[3] V_{BE} decreases by approximately 2 mV/K with increasing temperature.



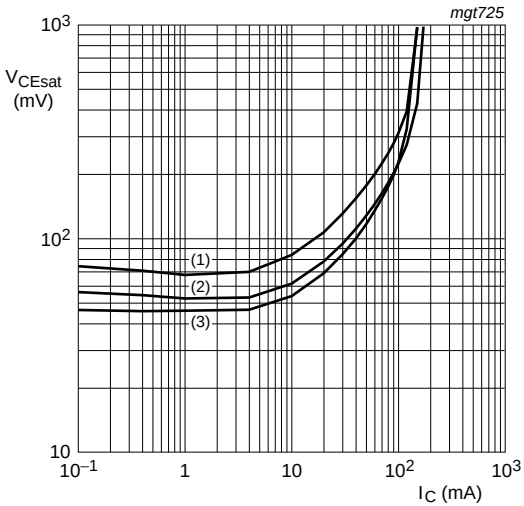
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 1. Selection A: DC current gain as a function of collector current; typical values



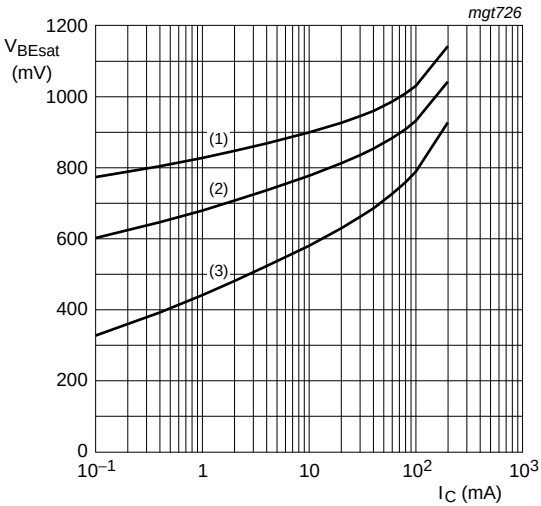
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 2. Selection A: Base-emitter voltage as a function of collector current; typical values



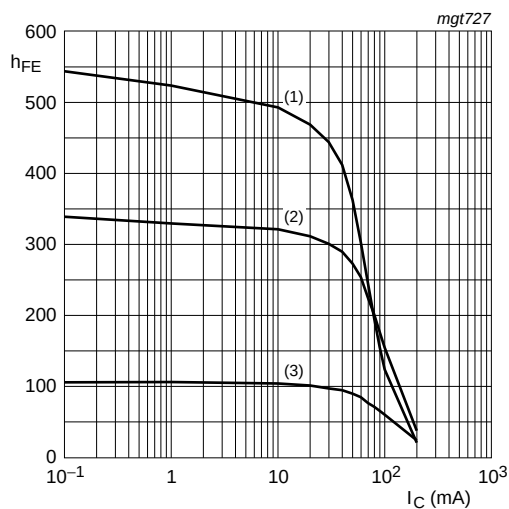
$I_C/I_B = 20$
(1) $T_{amb} = 150^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = -55^\circ\text{C}$

Fig 3. Selection A: Collector-emitter saturation voltage as a function of collector current; typical values



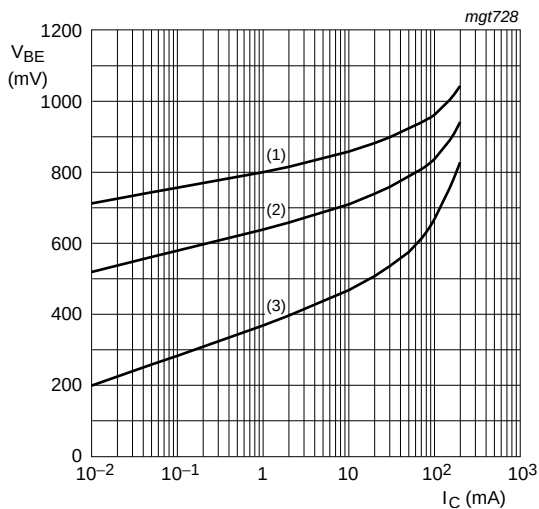
$I_C/I_B = 10$
(1) $T_{amb} = -55^\circ\text{C}$
(2) $T_{amb} = 25^\circ\text{C}$
(3) $T_{amb} = 150^\circ\text{C}$

Fig 4. Selection A: Base-emitter saturation voltage as a function of collector current; typical values



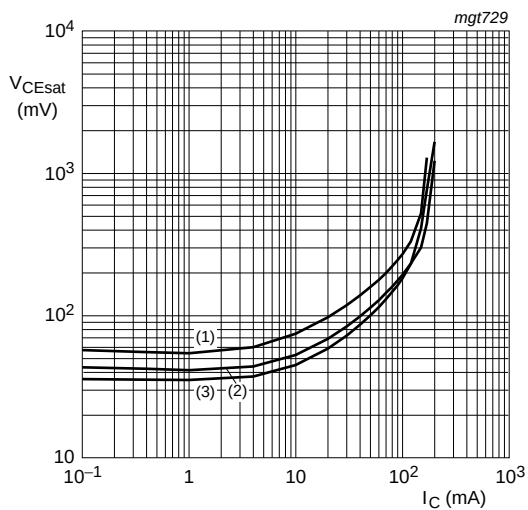
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

Fig 5. Selection B: DC current gain as a function of collector current; typical values



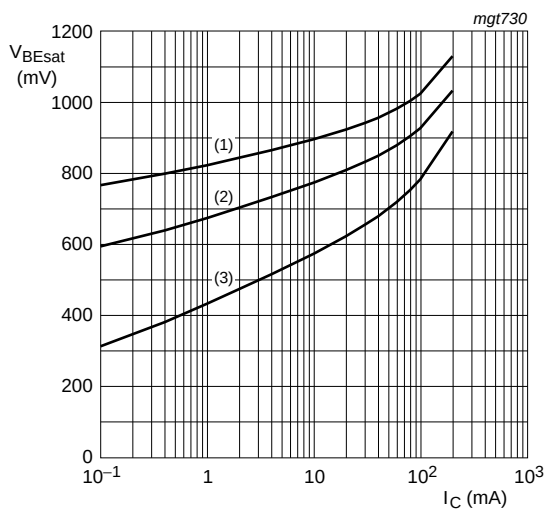
$V_{CE} = 5\text{ V}$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 6. Selection B: Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 20$
(1) $T_{amb} = 150\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = -55\text{ }^{\circ}\text{C}$

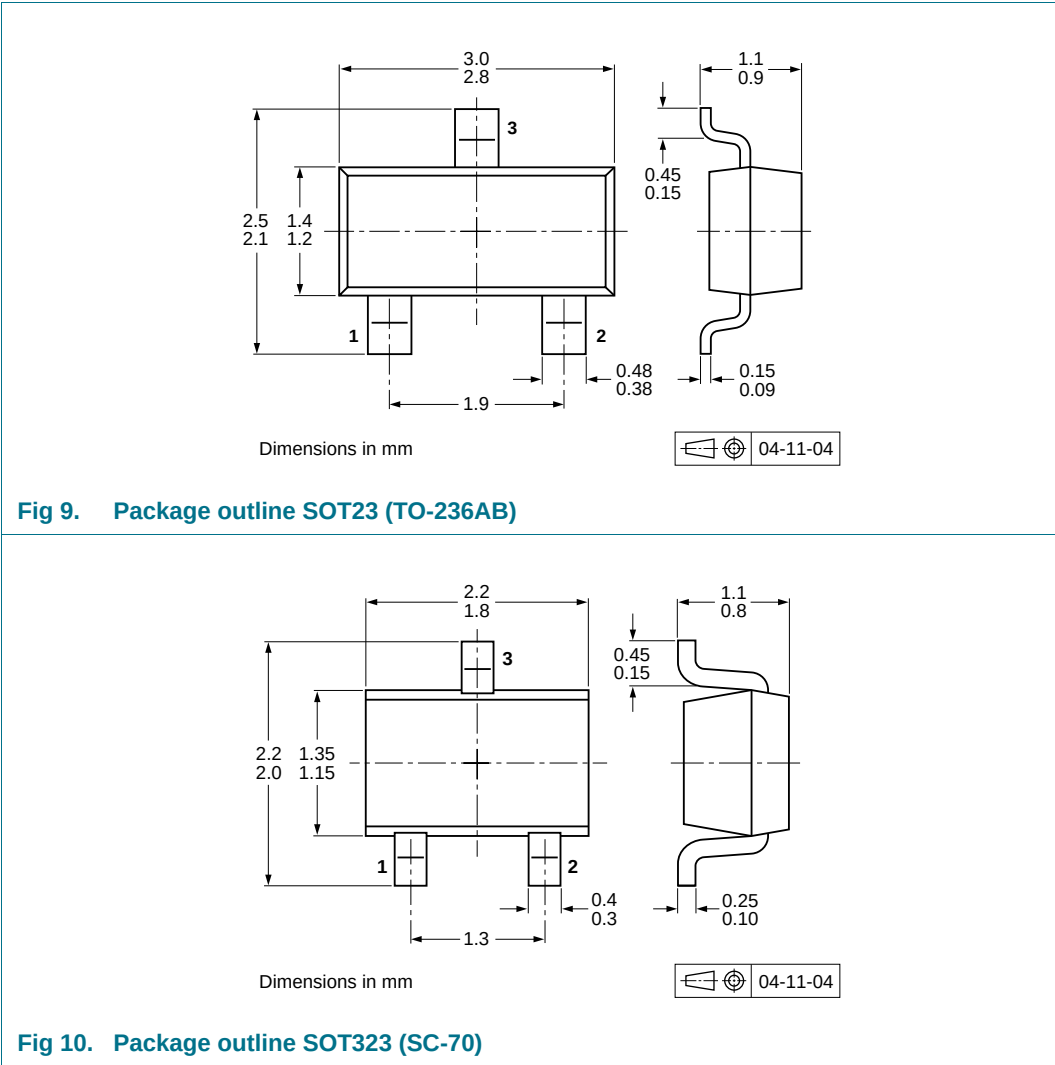
Fig 7. Selection B: Collector-emitter saturation voltage as a function of collector current; typical values

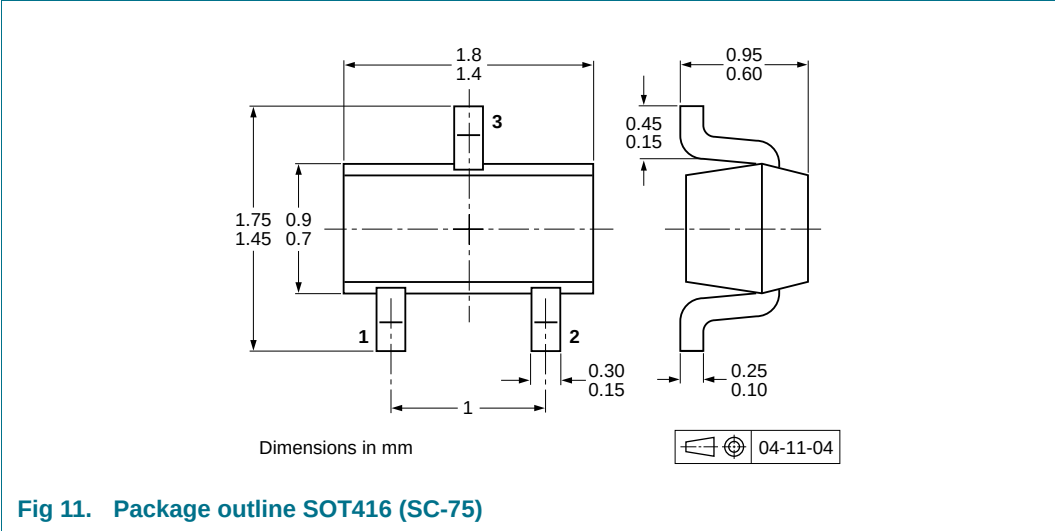


$I_C/I_B = 10$
(1) $T_{amb} = -55\text{ }^{\circ}\text{C}$
(2) $T_{amb} = 25\text{ }^{\circ}\text{C}$
(3) $T_{amb} = 150\text{ }^{\circ}\text{C}$

Fig 8. Selection B: Base-emitter saturation voltage as a function of collector current; typical values

8. Package outline





9. Packing information

Table 9. Packing methods
The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number ^[2]	Package	Description	Packing quantity		
			1000	3000	4000
BC846	SOT23	4 mm pitch, 8 mm tape and reel	-215	-	-235
BC846W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-	-135
BC846T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-	-135

[1] For further information and the availability of packing methods, see [Section 13](#).
[2] Valid for all available selection groups.

10. Soldering

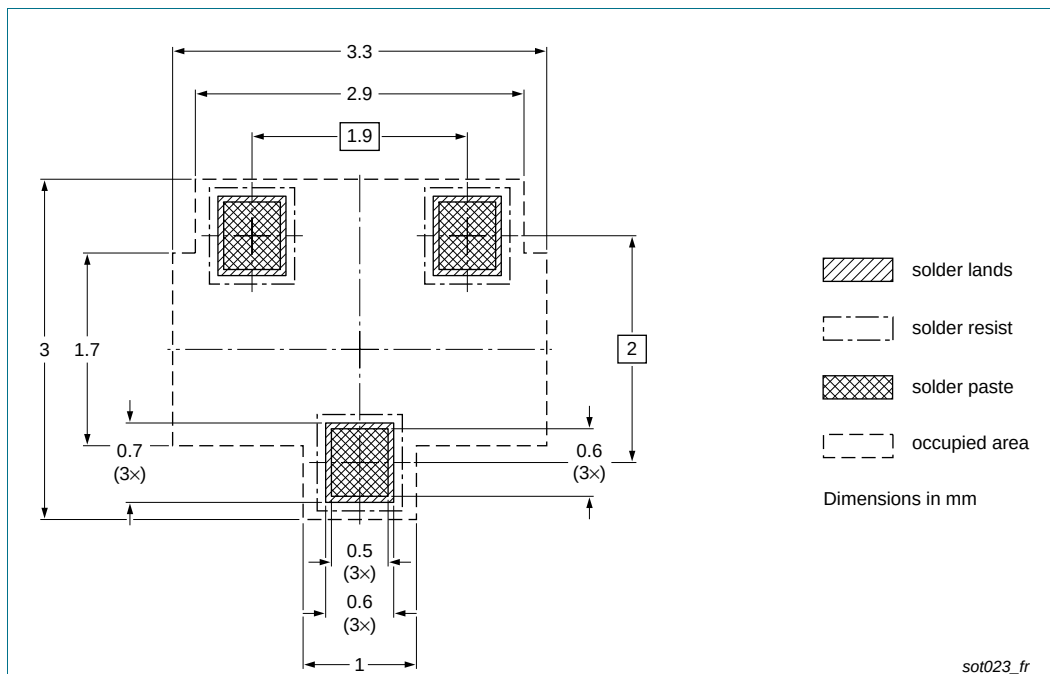


Fig 12. Reflow soldering footprint SOT23 (TO-236AB)

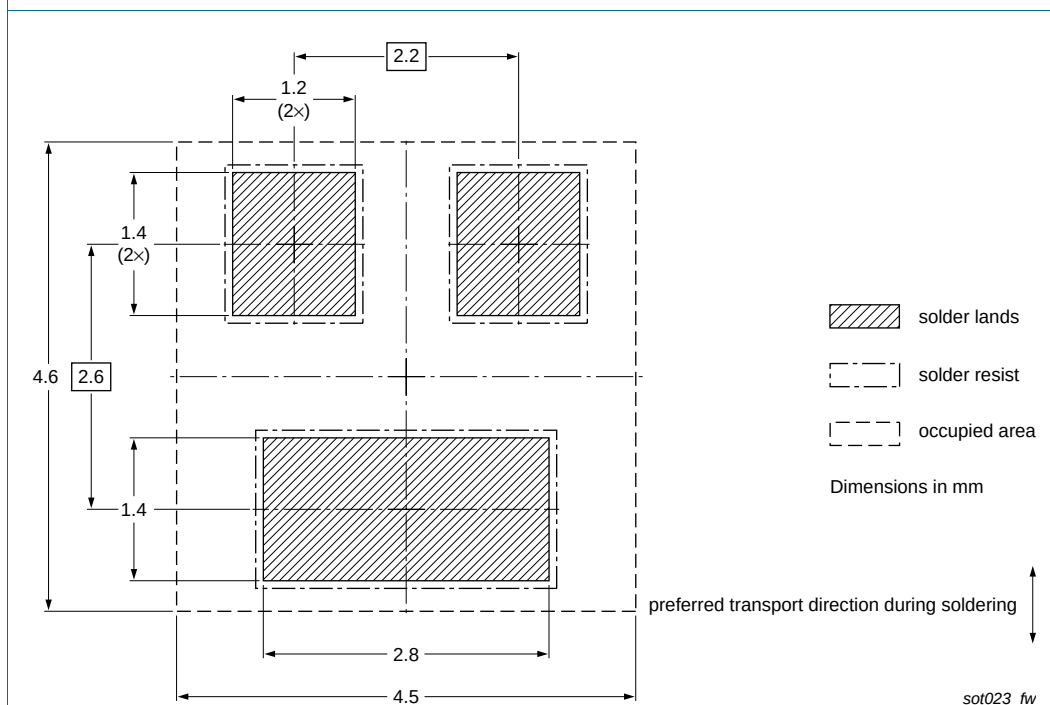


Fig 13. Wave soldering footprint SOT23 (TO-236AB)

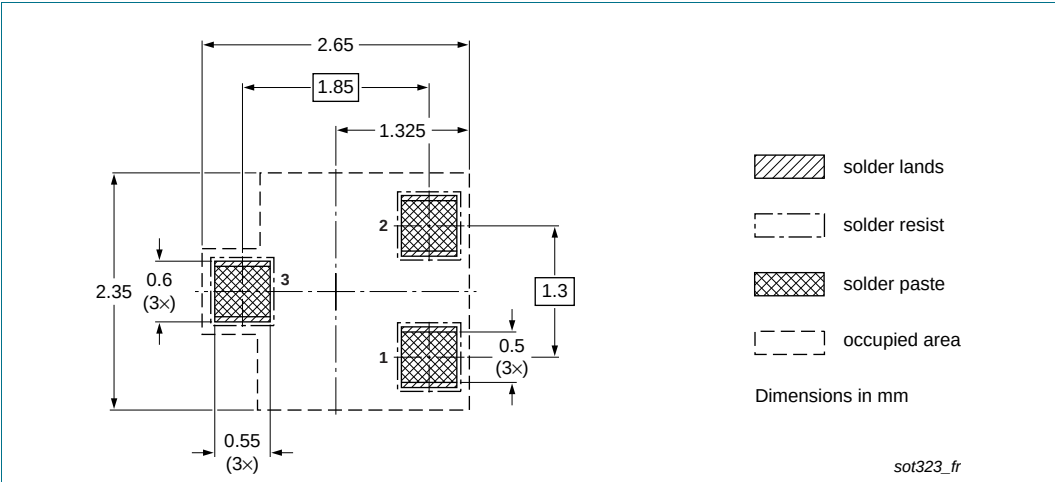


Fig 14. Reflow soldering footprint SOT323 (SC-70)

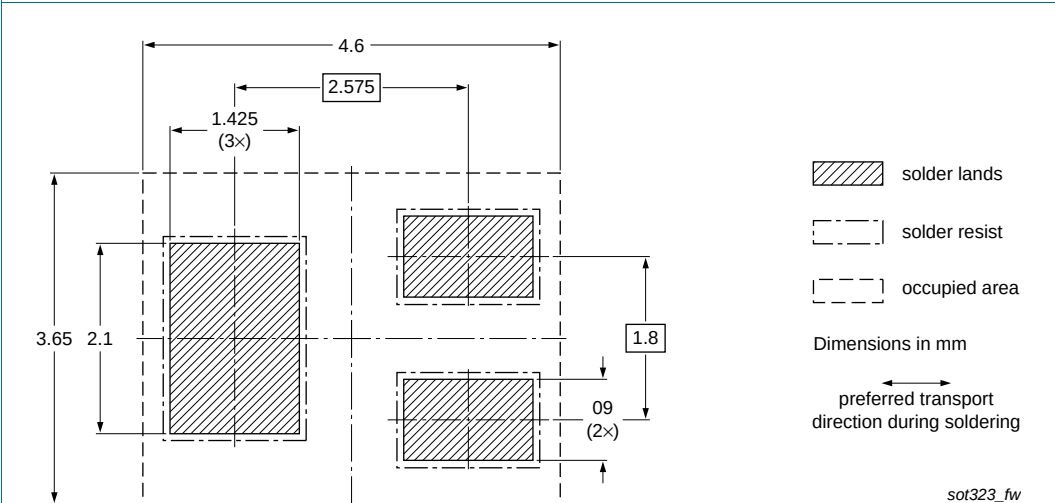
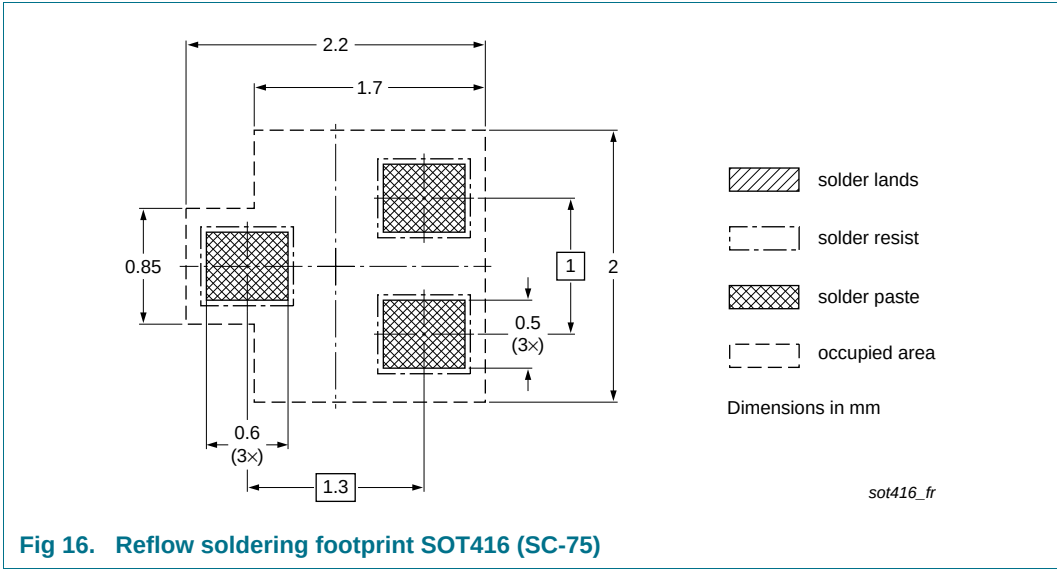


Fig 15. Wave soldering footprint SOT323 (SC-70)



11. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC846_SER v.9	20120925	Product data sheet	-	BC846_SER v.8
Modifications:	• Table 6 "Limiting values" : P_{tot} values corrected			
BC846_SER v.8	20120424	Product data sheet		BC846_BC546_SER v.7
BC846_BC546_SER v.7	20091117	Product data sheet	-	BC846_BC546_SER v.6
BC846_BC546_SER v.6	20060207	Product data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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